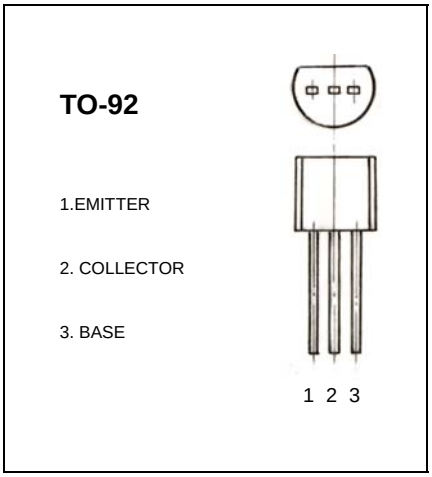
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

KTA1270 TRANSISTOR（ PNP ）



FEATURES

- **GENERAL PURPOSE APPLICATION SWITCHING APPLICATION**

MAXIMUM RATINGS* T_A=25℃ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.5	A
P_C	Collector Dissipation	500	mW
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100μA, I_E=0	-35			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -1 mA , I_B=0	-30			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -35 V , I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5 V , I_C=0			-0.1	μA
DC current gain	h_{FE1}	V_{CE}=-1 V, I_C= -100mA	70		240	
	h_{FE2}	V_{CE}=-6 V, I_C= -400mA	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -100mA, I_B= -10 mA			-0.25	V
Base-emitter voltage	$V_{BE(on)}$	V_{CE}= -1V, I_C= -100mA			-1	V
Transition frequency	f_T	V_{CE}=-6 V, I_C= -20mA F =100MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-6V,I_E=0,f=1MHz		13		pF

CLASSIFICATION OF h_{FE}

Rank		O	Y
Range	$h_{FE(1)}$	70-140	120-240
	$h_{FE(2)}$	25(min)	40(min)

Typical Characteristics

KTA1270